



S/N 09/652,619

PATENT

*Election*

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Gurtej Singh Sandhu et al.

Examiner: Renee Berry

Serial No.: 09/652,619

Group Art Unit: 2818

Filed: August 31, 2000

Docket: 303.085US4

Title: METHOD FOR FORMING A METALLIZATION LAYER

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**RESPONSE TO RESTRICTION REQUIREMENT**

Commissioner for Patents  
Washington, D.C. 20231

In response to the Restriction Requirement mailed May 22, 2001, Applicant elects, without traverse, Group I (claims 21-31). Applicant respectfully cancels remaining claims 32-54 (Group II-III) without prejudice, and reserves the right to reintroduce them in a divisional application at a later date.

**IN THE CLAIMS**

Please substitute the claim set in the appendix entitled Clean Version of Pending Claims for the previously pending claim set. The substitute claim set is intended to reflect addition of new claims 55-99.

55. (New) An integrated circuit, comprising:
- a substrate;
  - a first layer of material formed on the substrate, the first layer having contact vias extending through to the substrate;
  - a second layer formed on the first layer, the second layer lining the contact vias; and
  - a copper metallization layer formed on the second layer.
56. (New) The integrated circuit of claim 55, wherein the first layer of material includes doped polysilicon.
57. (New) The integrated circuit of claim 55, wherein the first layer of material includes undoped polysilicon.

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